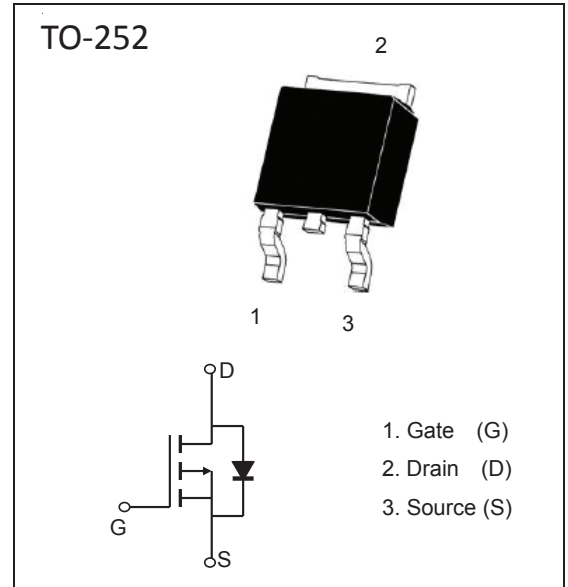


P-Channel MOSFET

RCD30P03

■ Features

- V_{DS} (V) = -30V
- I_D = -25A
- $R_{DS(ON)} < 35m\Omega$ @ $V_{GS} = -10V$ (Typ.:25m Ω)
- $R_{DS(ON)} < 54m\Omega$ @ $V_{GS} = -4.5V$ (Typ.:38m Ω)
- 100% EAS Guaranteed
- Green Device Available (RoHS Compliant)
- Super Low Gate Charge (Qg)
- Excellent dV/dt Effect Decline
- Advanced High Cell Density Trench Technology



■ Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D @ T_C = 25^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-25	A
$I_D @ T_C = 100^\circ C$	Continuous Drain Current, $V_{GS} @ -10V^1$	-15	A
I_{DM}	Pulsed Drain Current ²	-40	A
EAS	Single Pulse Avalanche Energy ³	25	mJ
I_{AS}	Avalanche Current	-10	A
$P_D @ T_A = 25^\circ C$	Total Power Dissipation ⁴	4.0	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ C$

P-Channel MOSFET RCD30P03

■ Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	35	°C/W

■ Electrical Characteristics($T_J=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=-250\mu A$	-30	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=-30V, V_{GS}=0V,$	-	-	-1	μA
I_{GSS}	Gate to Body Leakage Current	$V_{DS}=0V, V_{GS}=\pm 20V$	-	-	± 100	nA
On Characteristics						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=-250\mu A$	-1.0	-1.5	-2.5	V
$R_{DS(on)}$	Static Drain-Source on-Resistance <small>note3</small>	$V_{GS}=-10V, I_D=-7A$	-	25	35	m Ω
		$V_{GS}=-4.5V, I_D=-4A$	-	38	54	
Dynamic Characteristics						
C_{iss}	Input Capacitance	$V_{DS}=-15V, V_{GS}=0V,$ $f=1.0MHz$	-	982	-	pF
C_{oss}	Output Capacitance		-	135	-	pF
C_{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q_g	Total Gate Charge	$V_{DS}=-15V,$ $V_{GS}=-10V, I_D=-4A,$	-	10	-	nC
Q_{gs}	Gate-Source Charge		-	2	-	nC
Q_{gd}	Gate-Drain("Miller") Charge		-	2.7	-	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	$V_{DD}=-15V, I_D=-7A,$ $V_{GS}=-10V, R_{GEN}=2.5\Omega$	-	11	-	ns
t_r	Turn-on Rise Time		-	19	-	ns
$t_{d(off)}$	Turn-off Delay Time		-	45	-	ns
t_f	Turn-off Fall Time		-	26	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-25	A
I_{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-40	A
V_{SD}	Drain to Source Diode Forward Voltage	$V_{GS}=0V, I_S=-7A$	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$

P-Channel MOSFET RCD30P03

■ Typical Performance Characteristics

Figure 1: Output Characteristics

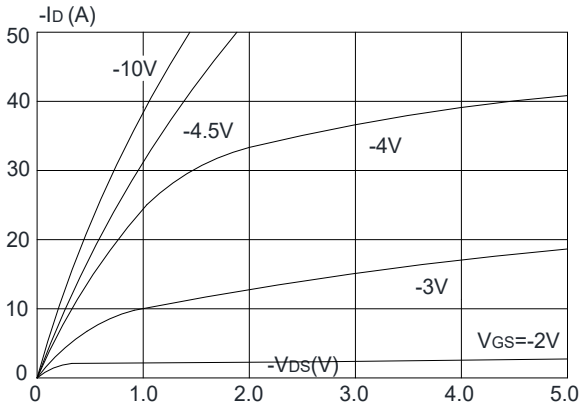


Figure 2: Typical Transfer Characteristics

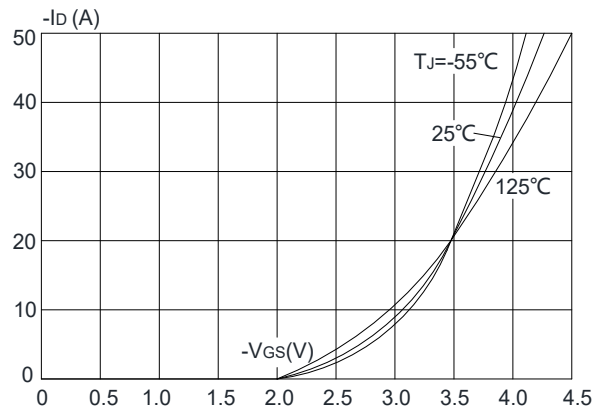


Figure 3: On-resistance vs. Drain Current

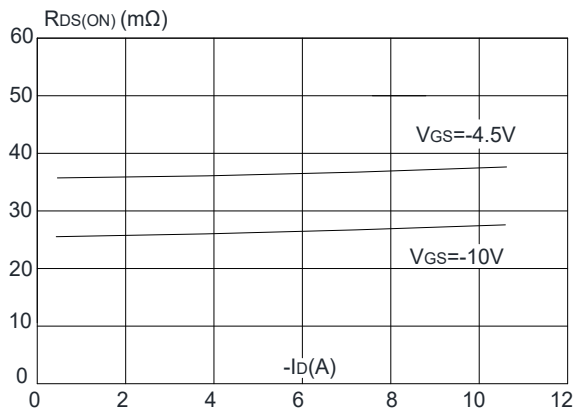


Figure 4: Body Diode Characteristics

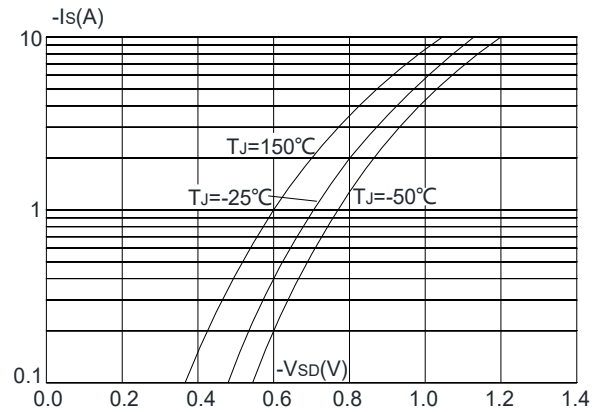


Figure 5: Gate Charge Characteristics

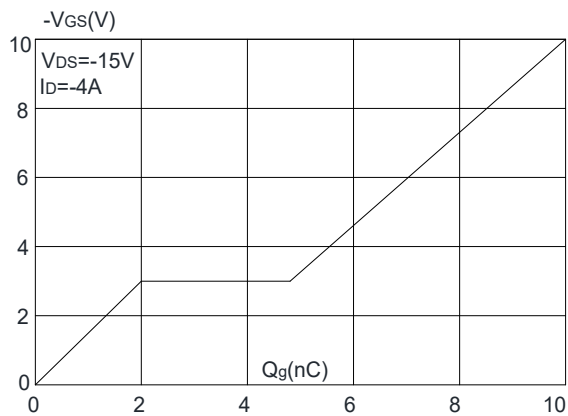
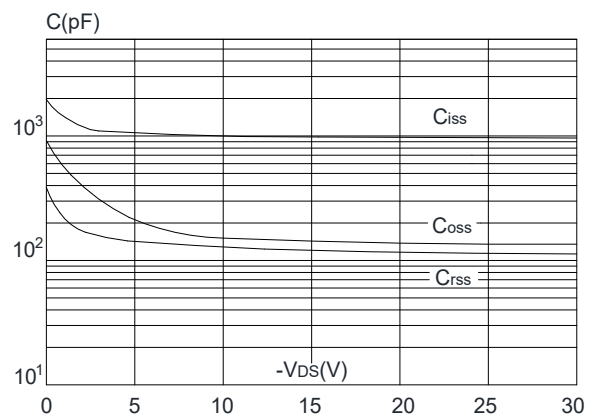


Figure 6: Capacitance Characteristics



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Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

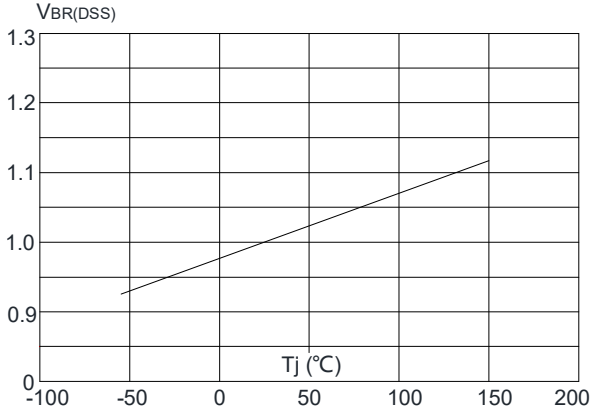


Figure 8: Normalized on Resistance vs. Junction Temperature

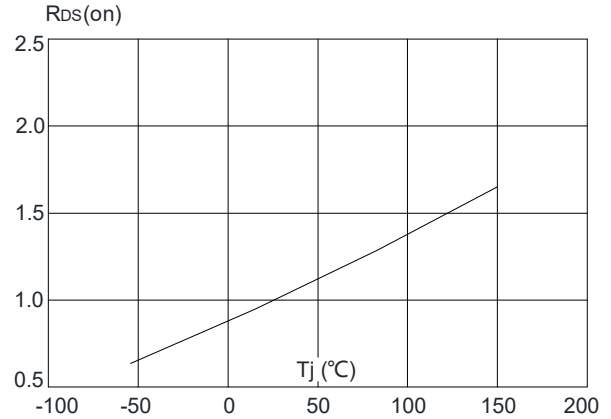


Figure 9: Maximum Safe Operating Area

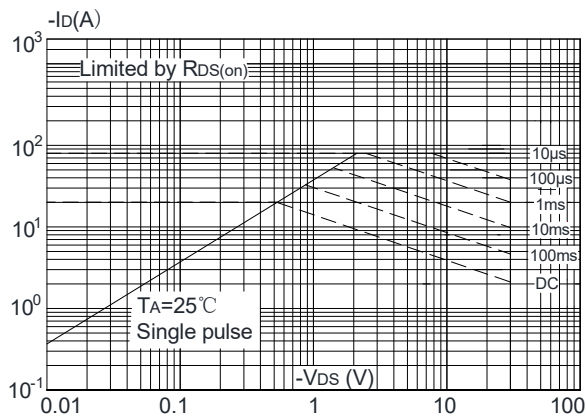


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

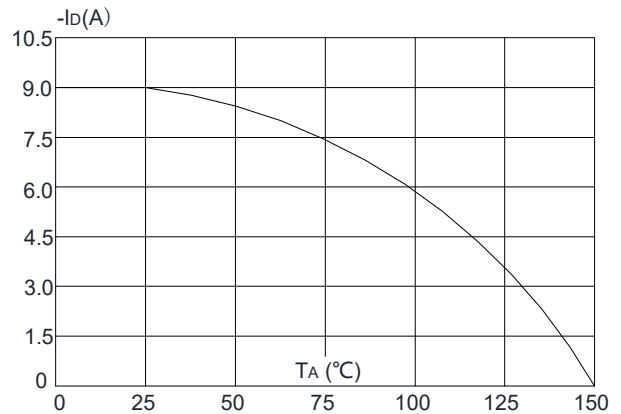
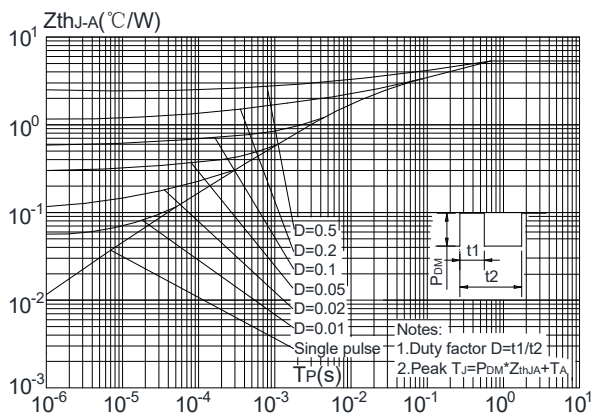


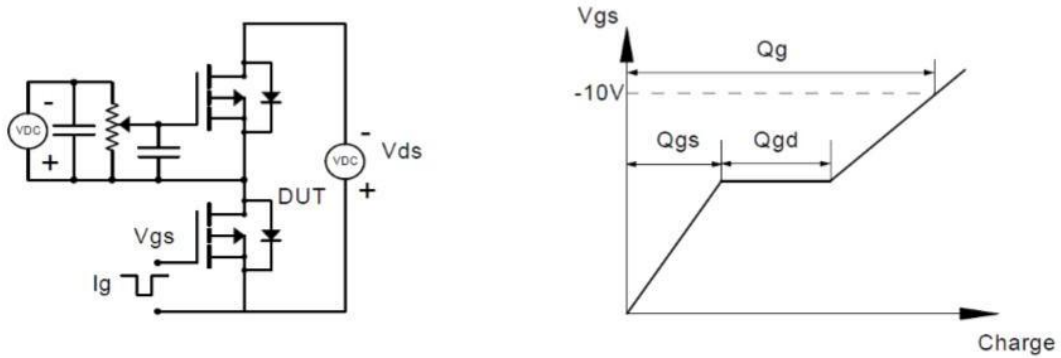
Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient



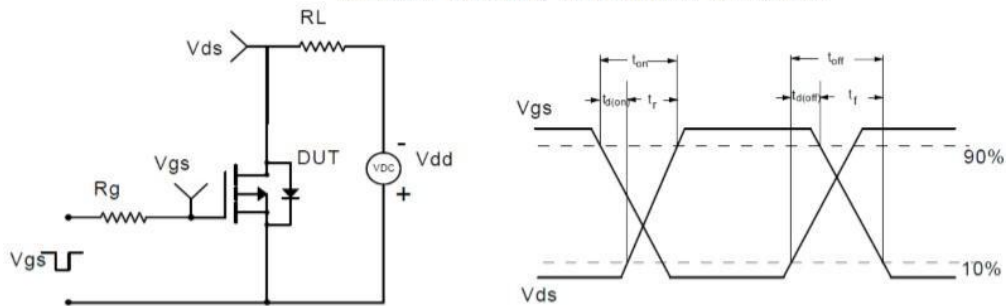
P-Channel MOSFET RCD30P03

■ Test Circuit

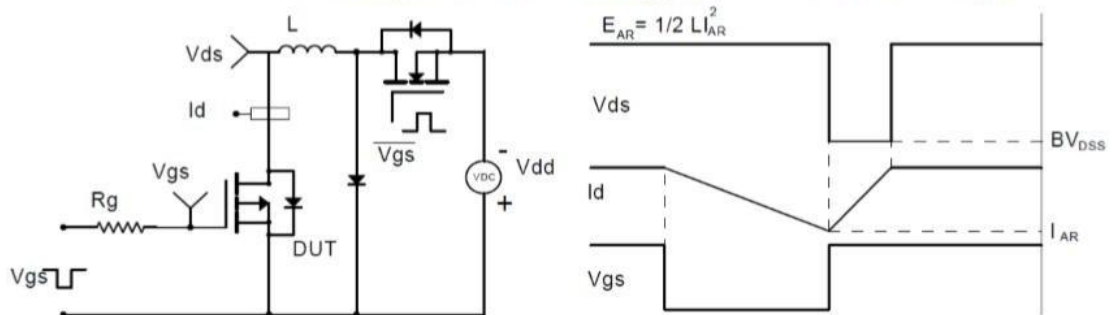
Gate Charge Test Circuit & Waveform



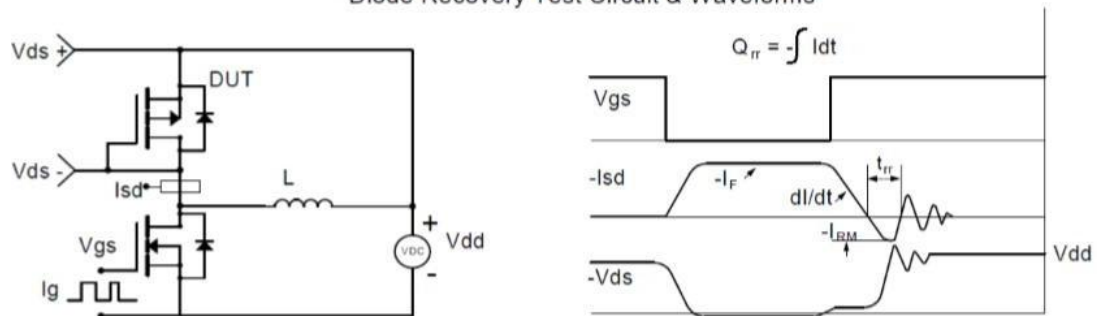
Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



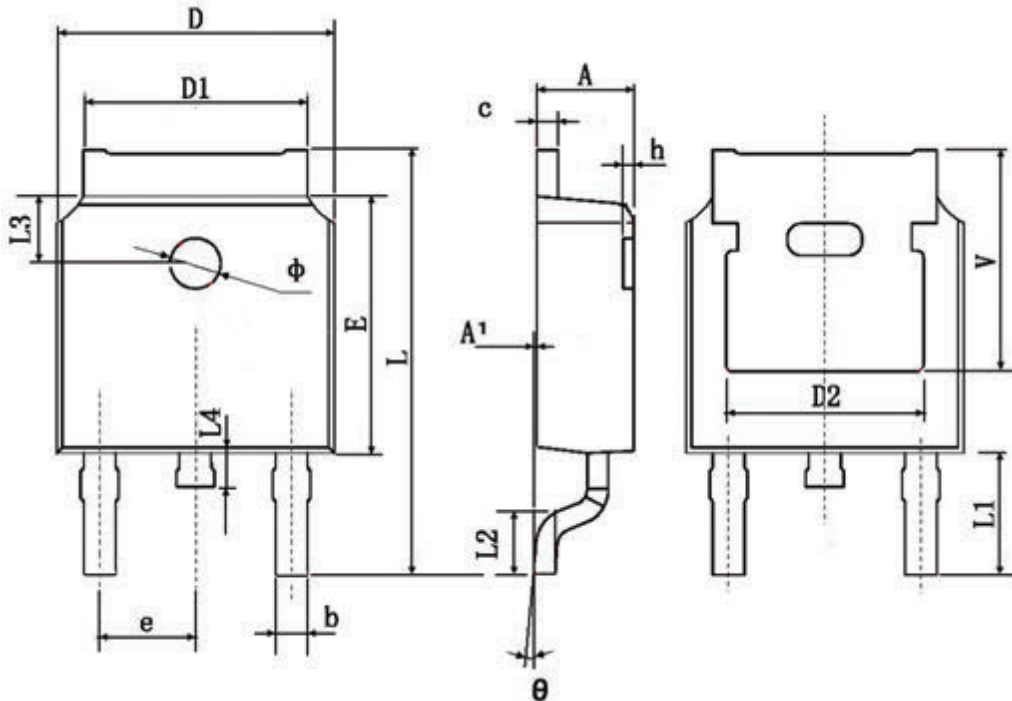
Diode Recovery Test Circuit & Waveforms



P-Channel MOSFET RCD30P03

■ Package Dimension

TO-252



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	